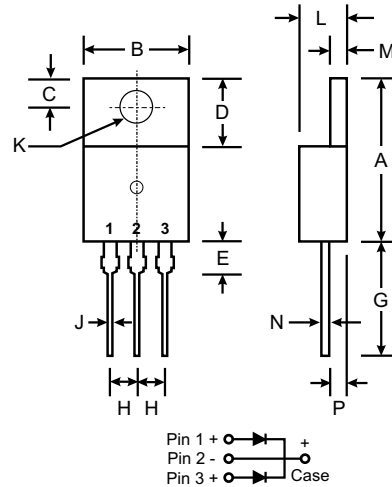


Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 2.24 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



TO-220AB		
Dim	Min	Max
A	14.22	15.88
B	9.65	10.67
C	2.54	3.43
D	5.84	6.86
E	—	6.35
G	12.70	14.73
H	2.29	2.79
J	0.51	1.14
K	3.53 \varnothing	4.09 \varnothing
L	3.56	4.83
M	1.14	1.40
N	0.30	0.64
P	2.03	2.92
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR2535CT	MBR2545CT	MBR2550CT	MBR2560CT	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	35	45	50	60	V
Working Peak Reverse Voltage	V _{RWM}					
DC Blocking Voltage	V _R					
RMS Reverse Voltage	V _{R(RMS)}	25	32	35	42	V
Average Rectified Output Current @ T _C = 130°C	I _O	30				A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	150				A
Peak Repetitive Reverse Surge Current (Note 3)	I _{RRM}	1.0		0.5		A
Forward Voltage Drop @ I _F = 15.0A, T _C = 25°C	V _{FM}	—		0.75		V
@ I _F = 15.0A, T _C = 125°C		—		0.65		
@ I _F = 30.0A, T _C = 25°C		0.82		—		
@ I _F = 30.0A, T _C = 125°C		0.73		—		
Peak Reverse Current at Rated DC Blocking Voltage @ T _C = 25°C	I _{RM}	0.2		1.0		mA
@ T _C = 125°C		40		50		
Typical Junction Capacitance (Note 2)	C _j	750		500		pF
Typical Thermal Resistance Junction to Case (Note 1)	R _{θJC}	1.5				°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150				°C

- Notes:
1. Thermal resistance junction to case mounted on heatsink.
 2. Measured at 1.0MHz and Applied Reverse Voltage of 4.0V DC.
 3. 2.0 μ s pulse width, f = 1.0KHz.

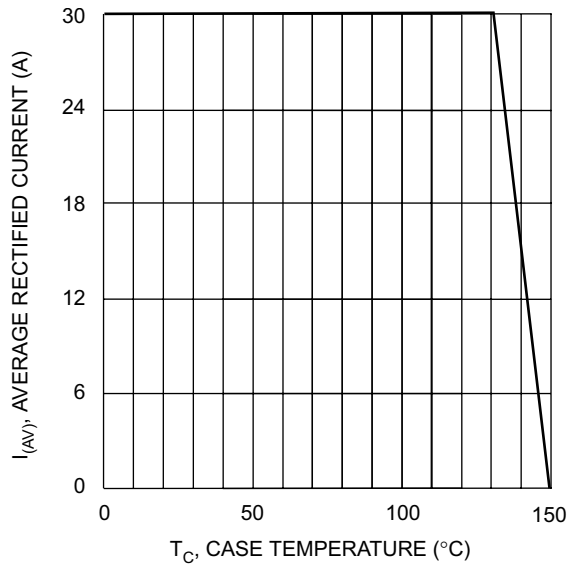


Fig. 1 Forward Derating Curve

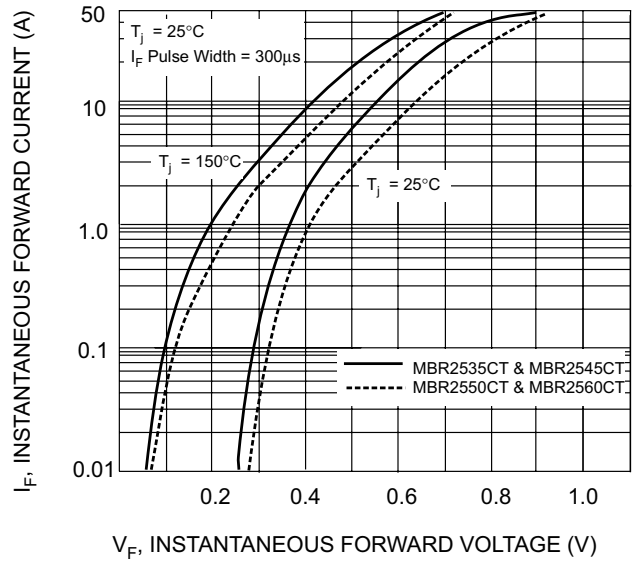


Fig. 2 Typical Forward Characteristics

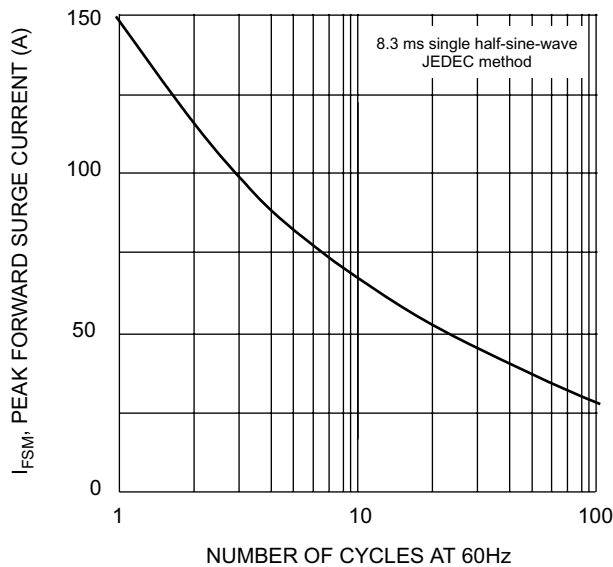


Fig. 3 Maximum Non-Repetitive Surge Current

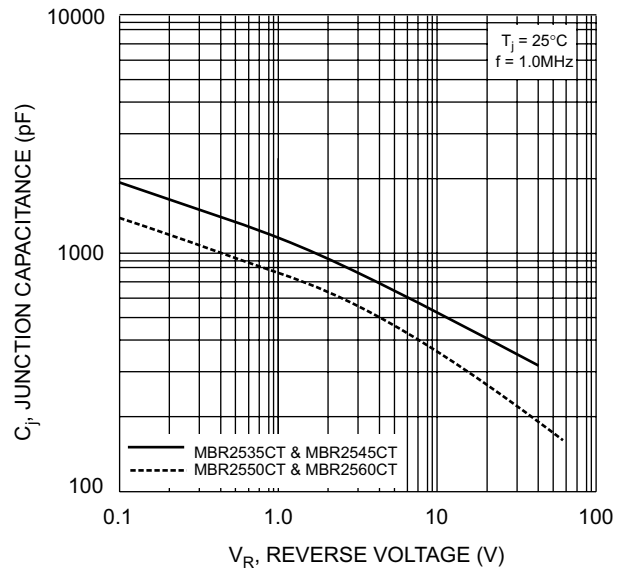


Fig. 4 Typical Junction Capacitance